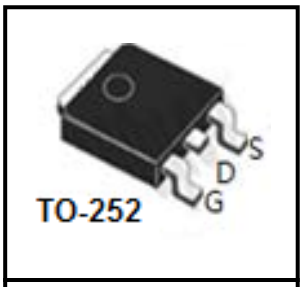
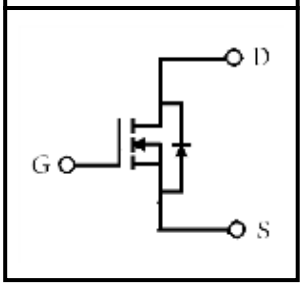
30V N-Channel Trench MOSFET

FEATURES

- Super Low Gate Charge
- 100% EAS Guaranteed
- RoHS compliant
- Green Device Available
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology





APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Hard switched and high frequency circuits

Device Marking and Package Information

Device	Package	Marking
CTD03N4P3	TO-252	CTD03N4P3

Absolute Maximum Ratings at T_j= 25ºC unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS} = 0V)	V_{DSS}	30	V
Drain Current-Continuous(Tc =25℃)	I_D	105	A
Drain Current-Continuous(Tc =100℃)		75	
Pulsed Drain Current	I_{DM}	370	A
Gate Source Voltage	V_{GSS}	±20	V
Single Pulse Avalanche Energy	E_{AS}	300	mJ
Power Dissipation T_C = 25ºC	P_D	85	W
Power Dissipation T_C = 100ºC		40	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+175	ºC

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance,Junction-to-Case (note1)	$R_{\theta JC}$	1.85	℃/W

Electrical Characteristics T_j= 25ºC unless otherwise specified						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V, T_J = 25ºC	--	--	1	uA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V, T_J = 55ºC	--	--	5	
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.5	2.5	V
Drain-Source On-Resistance (note2)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 30A	--	3.2	4.3	mΩ
		V_{GS} = 4.5V, I_D = 20A	--	5.3	7.0	mΩ
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1.0MHz	--	2150	--	pF
Output Capacitance	C_{oss}		--	328	--	
Reverse Transfer Capacitance	C_{rss}		--	281	--	
Total Gate Charge （4.5V）	Q_g	V_{DS} = 25V, I_D = 30A, V_{GS} = 10V	--	39.8	--	nC
Gate-Source Charge	Q_{gs}		--	3.2	--	
Gate-Drain Charge	Q_{gd}		--	13.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 15V, R_L = 0.75Ω V_{GS} = 10V,R_G = 3Ω	--	22.8	--	ns
Turn-on Rise Time	t_r		--	33.5	--	
Turn-off Delay Time	$t_{d(off)}$		--	56	--	
Turn-off Fall Time	t_f		--	32.6	--	
Body Diode Characteristics						
Continuous Body Diode Current	I_{SD}	T_C = 25 ºC	--	--	105	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 20A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	t_{rr}	TJ=25℃ I_F=30A, di/dt=100A/μs	--	14.3	--	nS
Reverse Recovery Charge	Q_{rr}		--	4.1	--	NC

Notes

1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width≦300us , duty cycle≦2%

3.The EAS data shows Max. rating . The test condition is VDD =25V,VGS =10V,L=0.5mH

4.The power dissipation is limited by 175℃ junction temperature

5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics T_J = 25ºC, unless otherwise noted

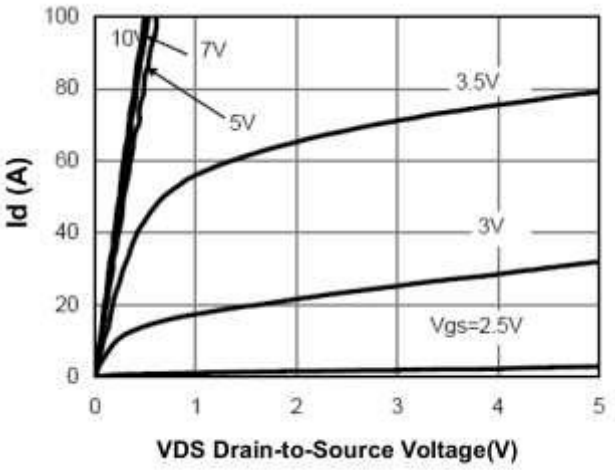


Fig.1 Typical Output Characteristics

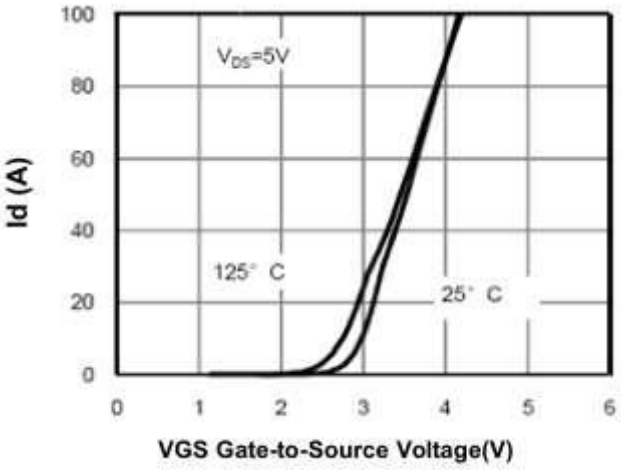


Fig.2 On-Resistance vs. G-S Voltage

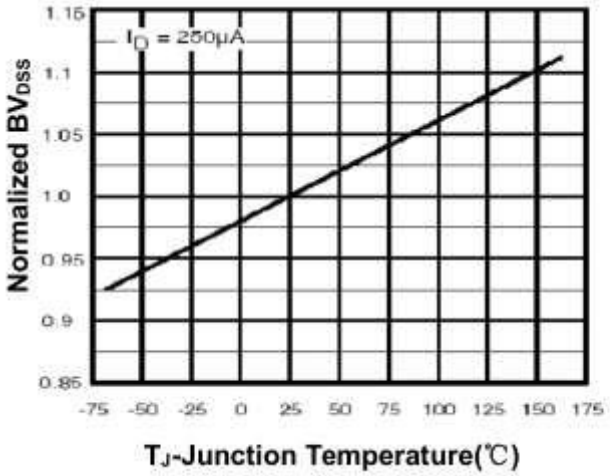


Fig.3 Source Drain Forward Characteristics

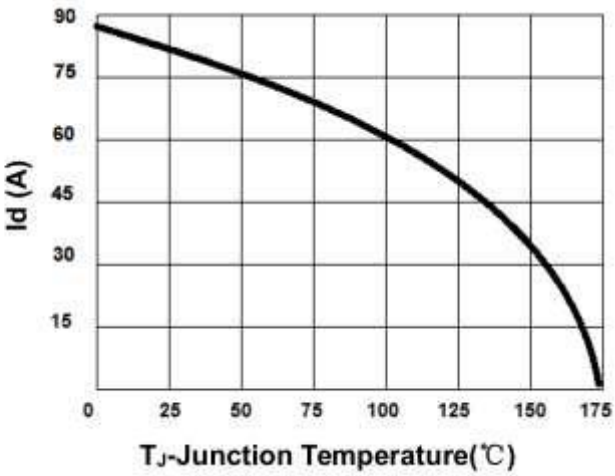


Fig.4 Gate-Charge Characteristics

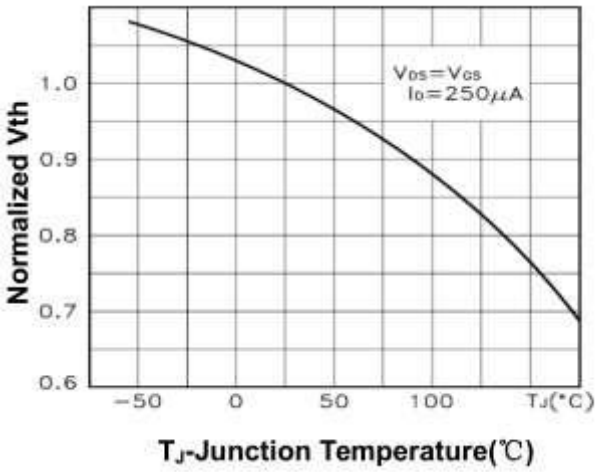


Fig.5 Normalized VGS(th) vs. TJ

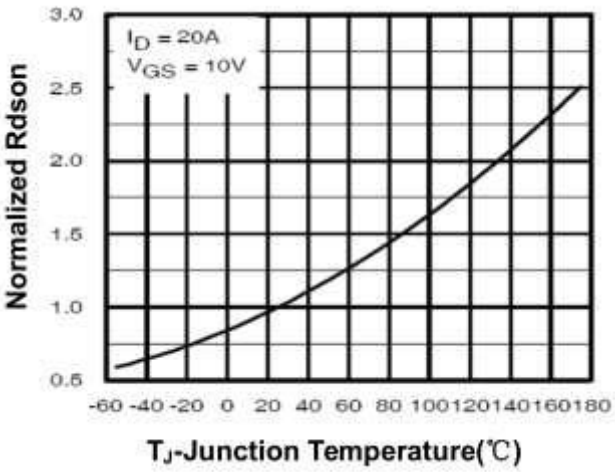


Fig.6 Normalized RDSON vs. TJ

Typical Characteristics T_J = 25ºC, unless otherwise noted

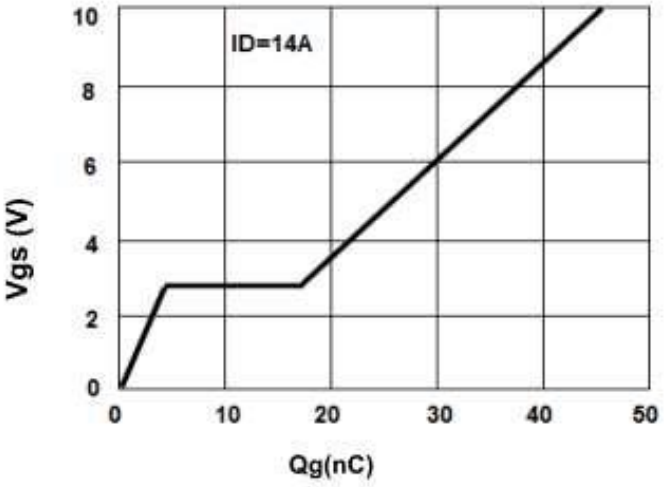


Figure 7. Gate Charge Waveforms

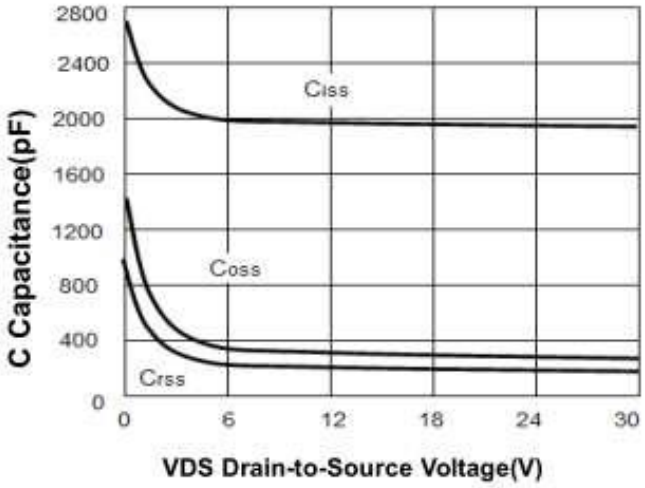


Figure 8. Capacitance

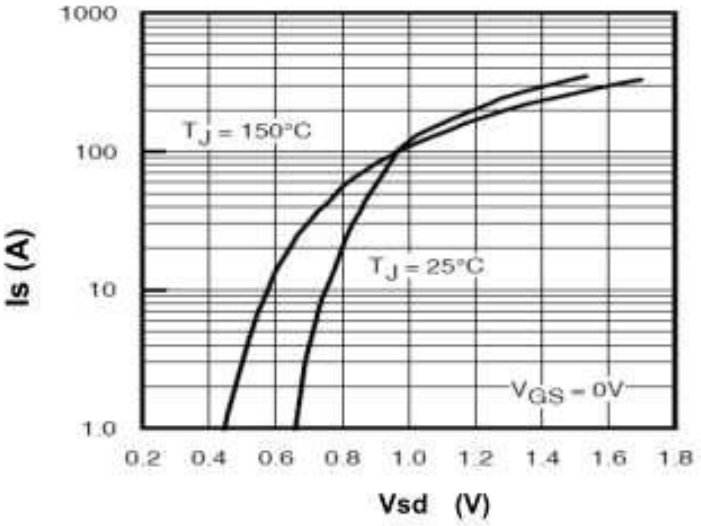


Figure 9: Body-Diode Characteristics

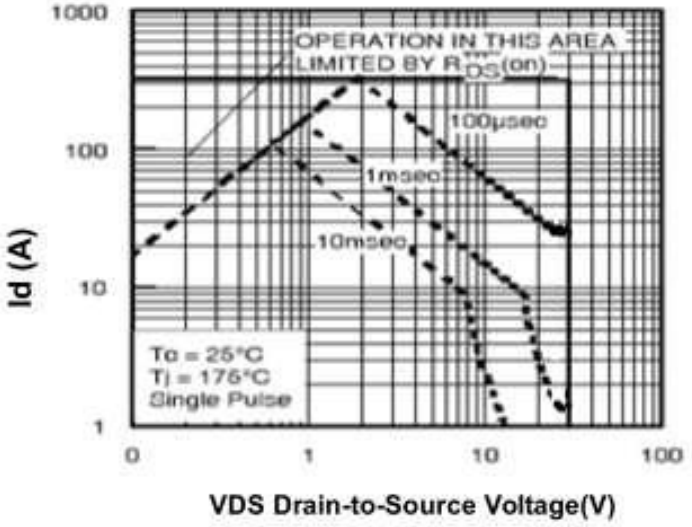


Figure 10: Maximum Safe Operating Area

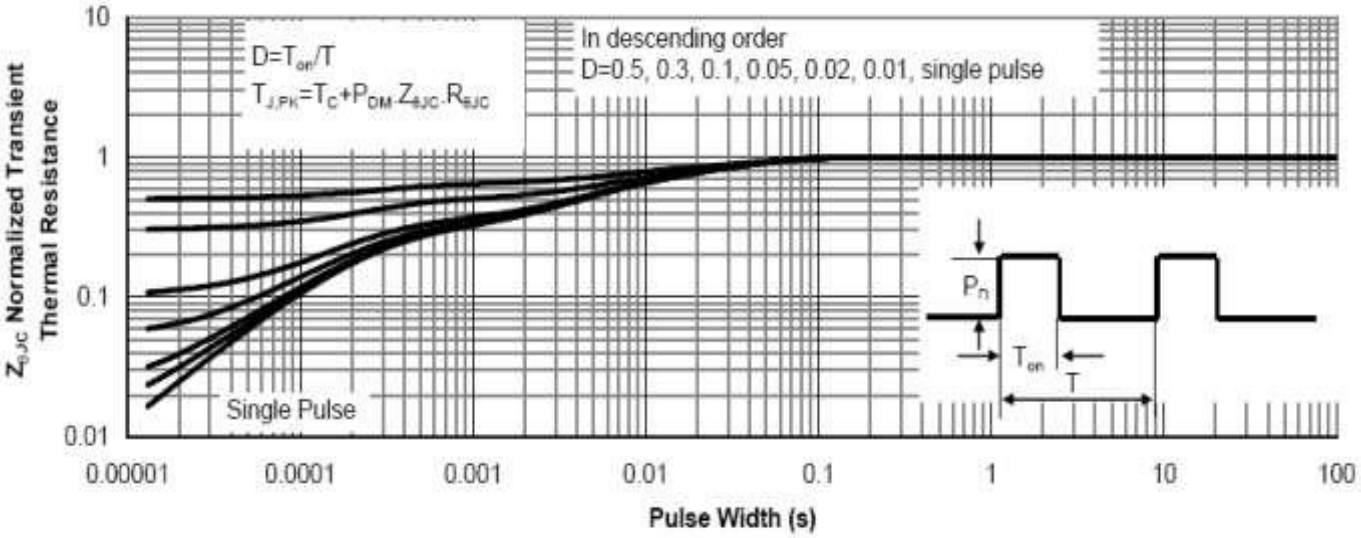


Figure.11: Normalized Maximum Transient Thermal Impedance

Figure A：Gate Charge Test Circuit and Waveform

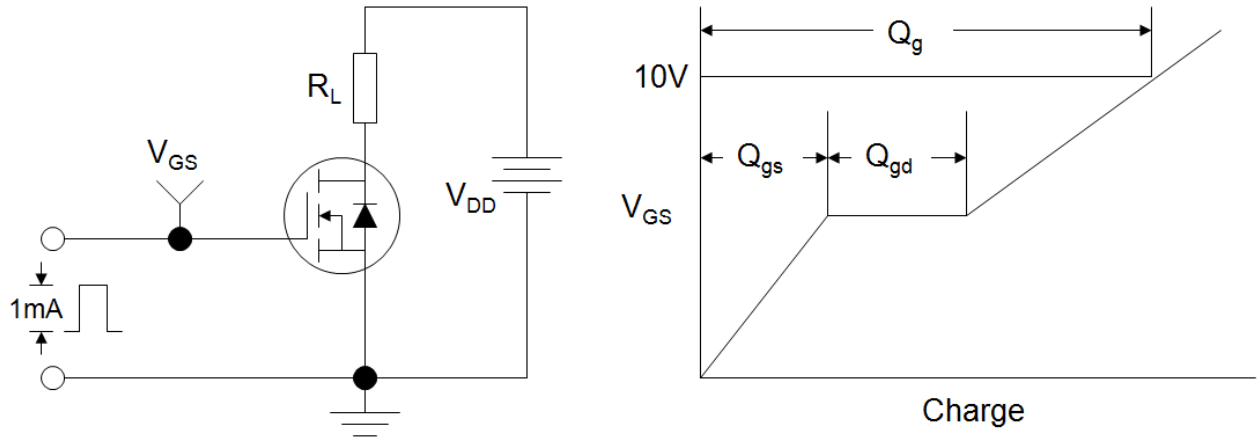


Figure B：Resistive Switching Test Circuit and Waveform

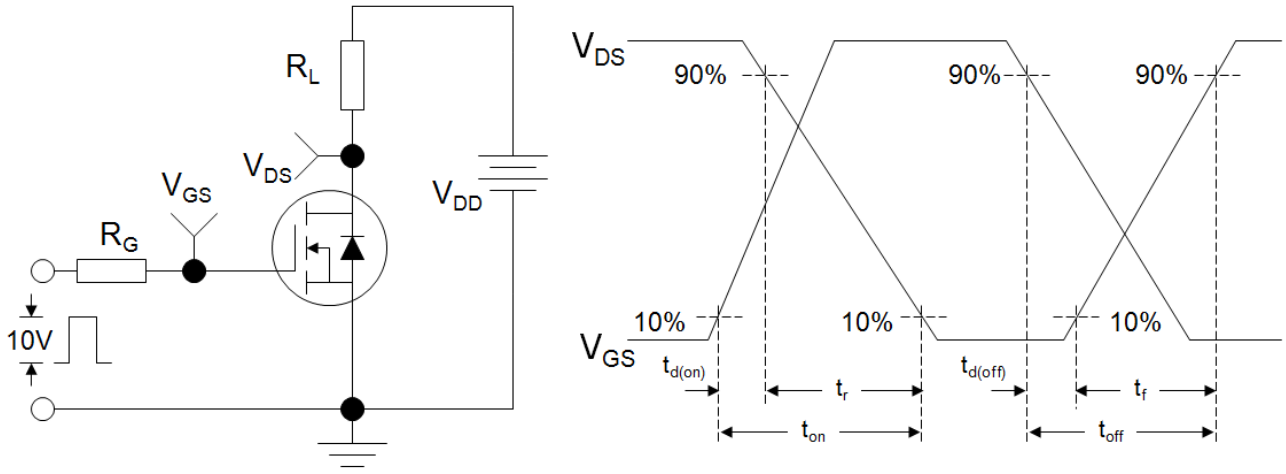
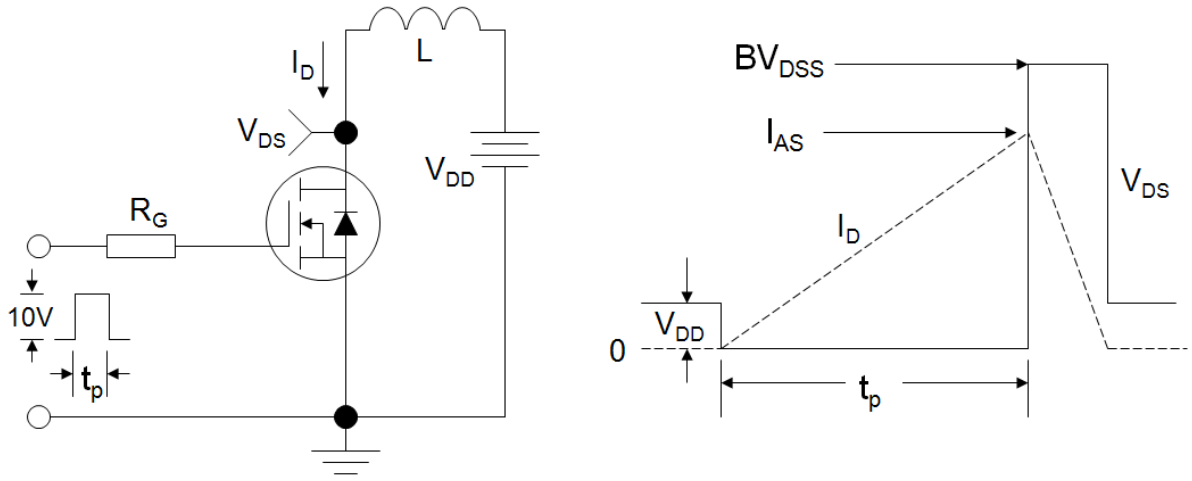


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



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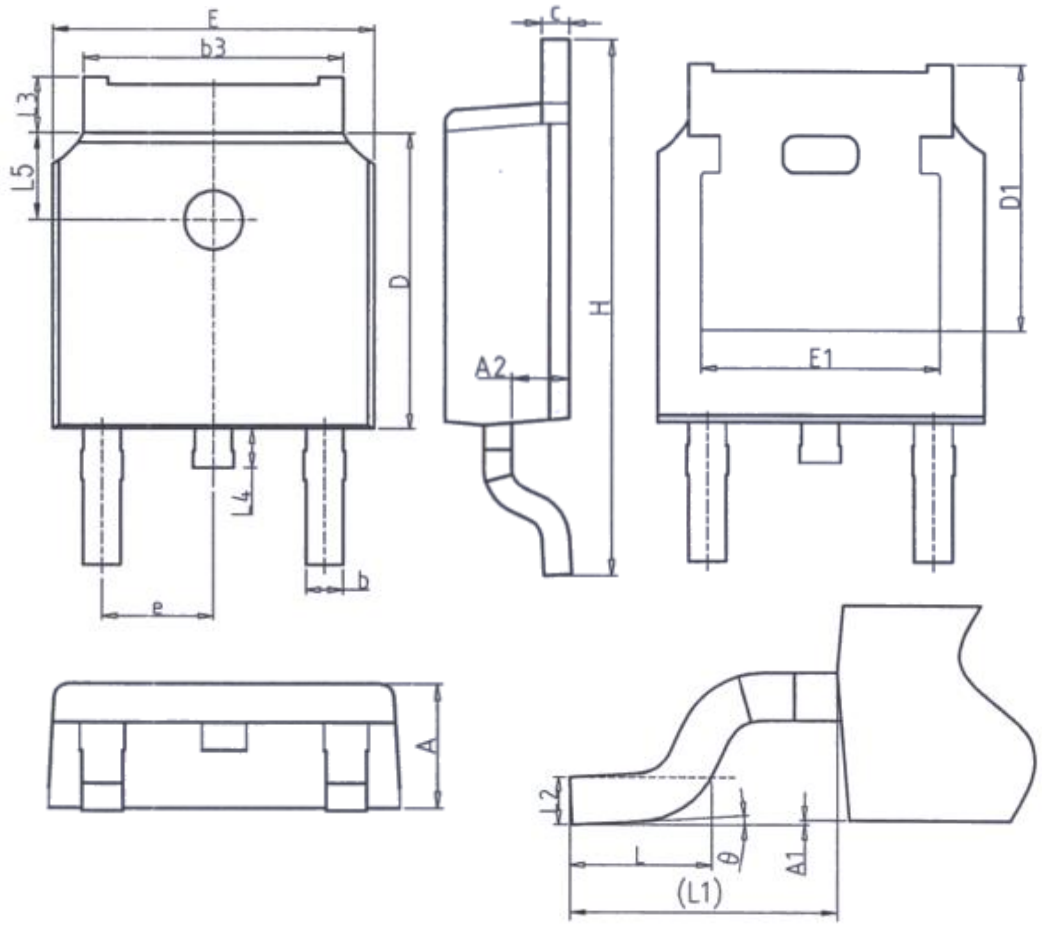

Unit: mm		
Symbol	Min.	Max.
A	2.20	2.40
A1	0.00	0.20
A2	0.97	1.17
b	0.68	0.90
b3	5.20	5.50
c	0.43	0.63
D	5.98	6.22
D1	5.30REF	
E	6.40	6.80
E1	4.63	–

Unit: mm		
Symbol	Min.	Max.
e	2.286BSC	
H	9.40	10.50
L	1.38	1.75
L1	2.90REF	
L2	0.51BSC	
L3	0.88	1.28
L4	–	1.00
L5	1.65	1.95
θ	0°	8°

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